

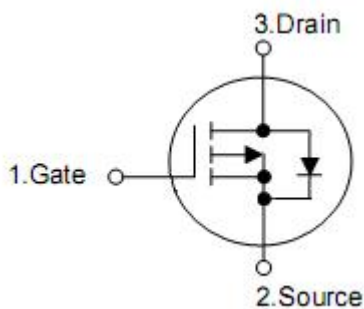
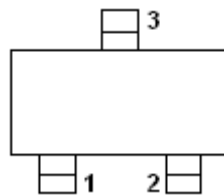
1. Description

The KIA3407 uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge. This device is suitable for use as a load switch or in PWM applications. Standard Product KIA3407 is Pb-free (meets ROHS & Sony 259 specifications). KIA3407 is a Green Product ordering option.

2. Features

- n $V_{DS}(V) = -30V$
- n $I_D = -4.1A$
- n $R_{DS(on)} < 60m\Omega (V_{GS} = -10V, I_D = -4.1A)$
- n $R_{DS(on)} < 90m\Omega (V_{GS} = -4.5V, I_D = -3.0A)$

3. Symbol



Pin	Function
1	Gate
2	Source
3	Drain

4. Absolute maximum ratings

($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-source voltage	V_{DS}	-30	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current ^A	I_D	$T_A=25^{\circ}\text{C}$	-4.1
		$T_A=70^{\circ}\text{C}$	-3.5
Pulsed drain current ^B	I_{DM}	-20	A
Total power dissipation ^A	P_D	$T_A=25^{\circ}\text{C}$	1.4
		$T_A=70^{\circ}\text{C}$	1
Junction and storage temperature range	T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$

5. Thermal characteristics

Parameter	Symbol	Typ	Max	Unit
Maximum junction-ambient ^A ($t \leq 10\text{s}$)	$R_{\theta JA}$	65	90	$^{\circ}\text{C}/\text{W}$
Maximum junction-ambient ^A	$R_{\theta JA}$	85	125	$^{\circ}\text{C}/\text{W}$
Maximum junction-Lead ^C	$R_{\theta JL}$	43	60	$^{\circ}\text{C}/\text{W}$

6. Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA
		$T_J=55^\circ C$	-	-	-5	
Gate- body leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.8	-3	V
On state drain current	$I_{D(on)}$	$V_{GS}=-4.5V, V_{DS}=-5V$	-10	-	-	A
Static drain-source on-resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4.1A$	-	-	60	$m\Omega$
		$V_{GS}=-4.5V, I_D=-3.0A$	-	-	90	
Forward transconductance	g_{fs}	$V_{DS}=-5.0V, I_D=-4.0A$	5.5	8.2	-	S
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-0.77	-1.0	V
Maximum body-diode continuous current	I_S		-	-	-2.2	A
Input capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $f=1MHz$	-	700	840	pF
Output capacitance	C_{oss}		-	120	-	
Reverse transfer capacitance	C_{rss}		-	75	-	
Gate resistance	R_g	$V_{DS}=0V,$ $V_{GS}=0V, f=1MHz$	-	10	15	Ω
Total gate charge(10V)	Q_g	$V_{DS}=-15V, V_{GS}=-4.5V$ $I_D=-4.0A$	-	14.3	18	nC
Total gate charge(4.5V)	Q_g		-	7	-	
Gate-source charge	Q_{gs}		-	3.1	-	
Gate-drain charge	Q_{gd}		-	3	-	
Turn-on delay time	$t_{d(on)}$	$V_{DS}=-15V, R_L=3.6\Omega,$ $R_G=3\Omega, V_{GS}=-10V$	-	8.6	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	28.2	-	
Fall time	t_f		-	13.5	-	
Reverse recovery time	t_{rr}	$I_F=-4A, di/dt=100A/\mu s,$	-	27	36	nS
Reverse recovery charge	Q_{rr}		-	15	-	nC

7. Test circuits and waveforms

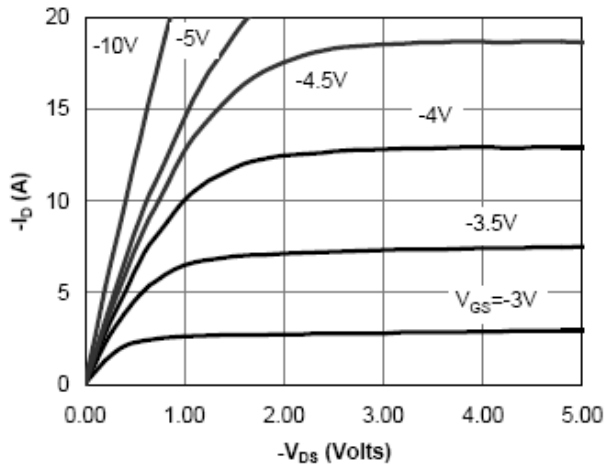


Figure 1: On-Region Characteristics

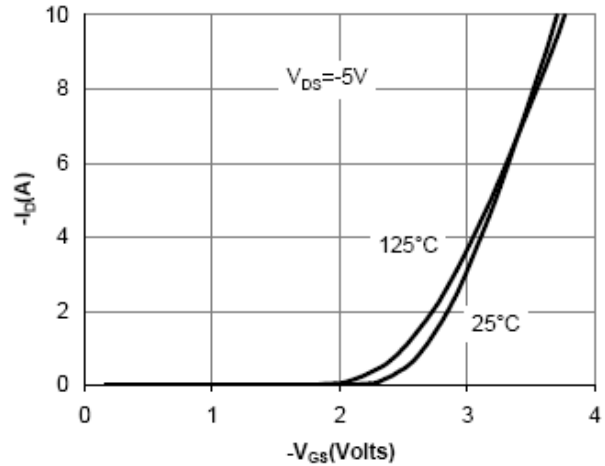


Figure 2: Transfer Characteristics

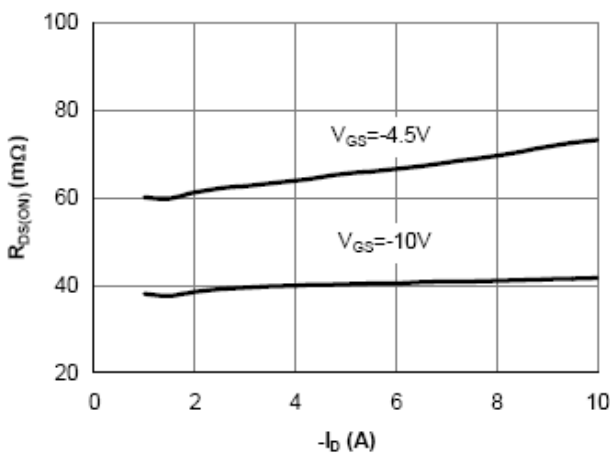


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

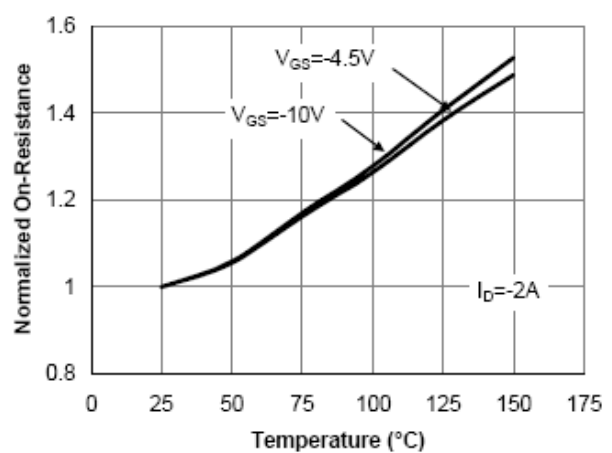


Figure 4: On-Resistance vs. Junction Temperature

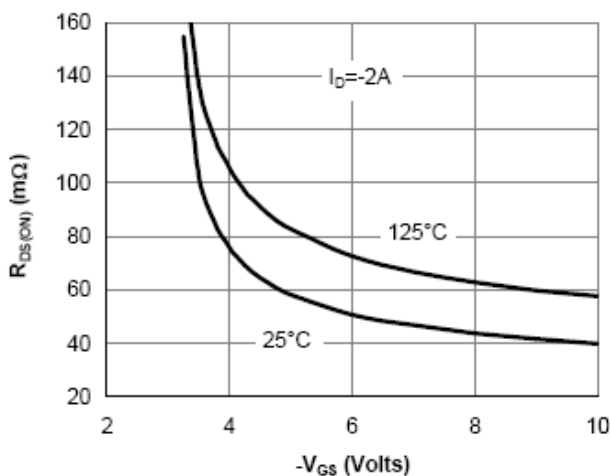


Figure 5: On-Resistance vs. Gate-Source Voltage

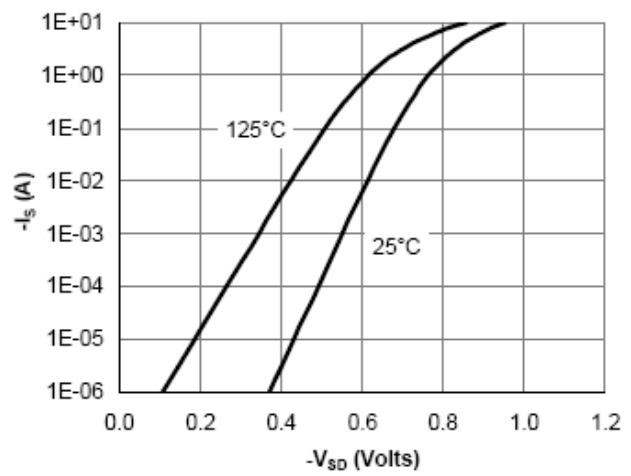


Figure 6: Body-Diode Characteristics

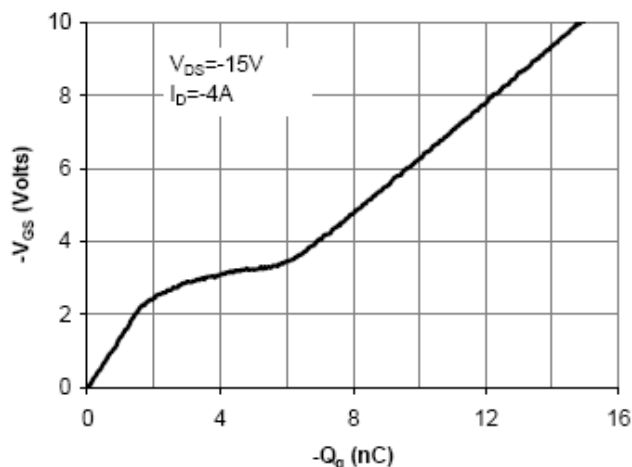


Figure 7: Gate-Charge Characteristics

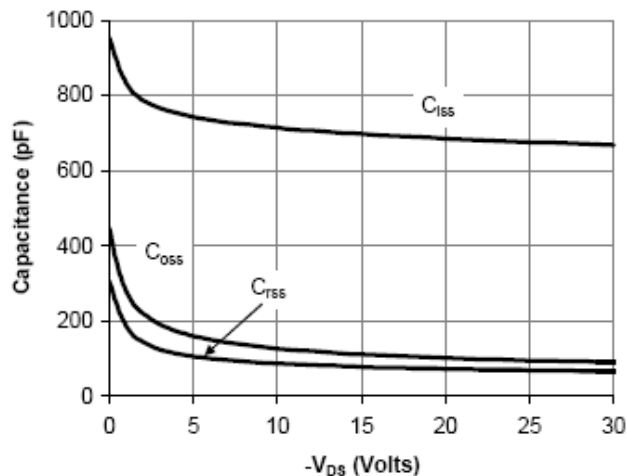


Figure 8: Capacitance Characteristics

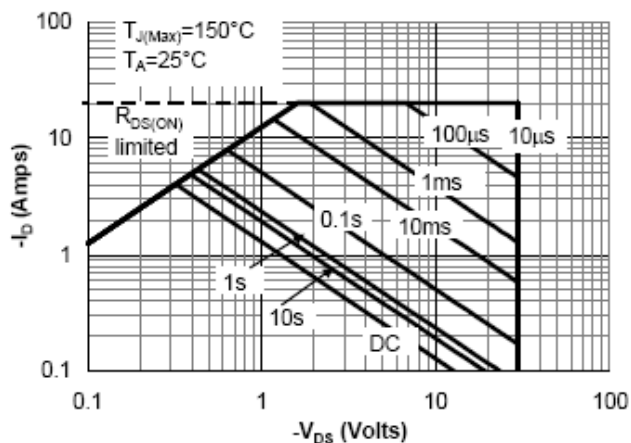


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

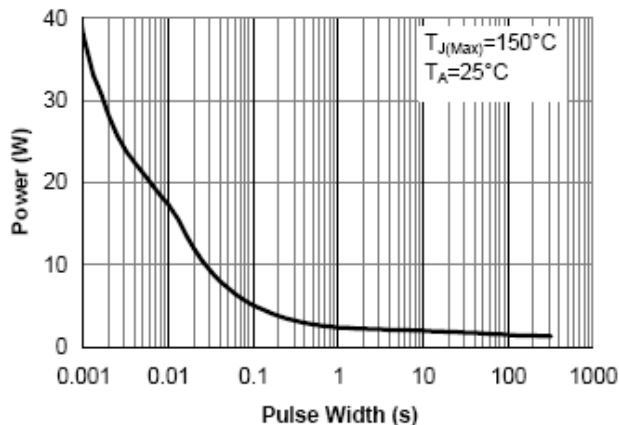


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

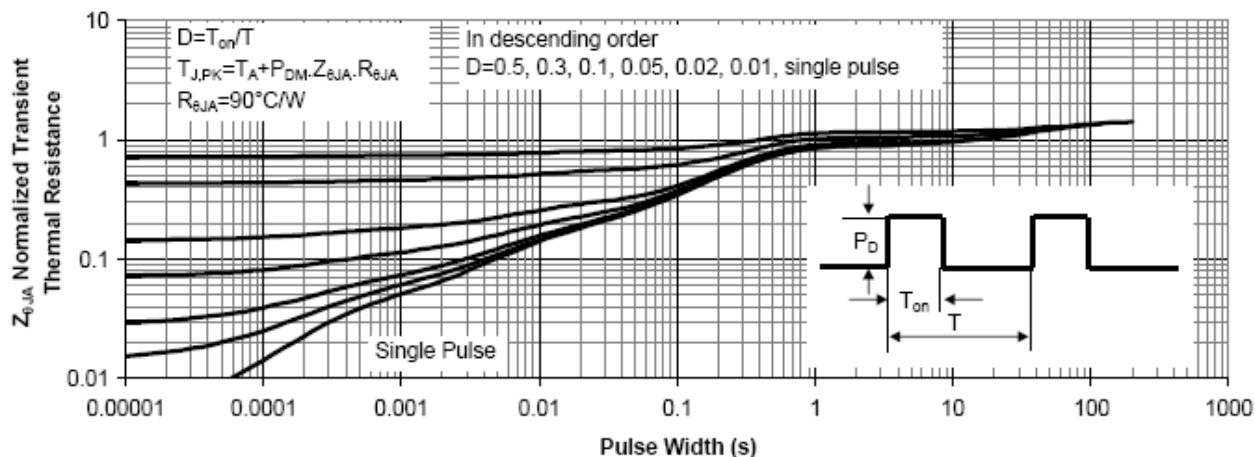


Figure 11: Normalized Maximum Transient Thermal Impedance